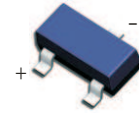


CDST4448-G

High Speed

RoHS Device

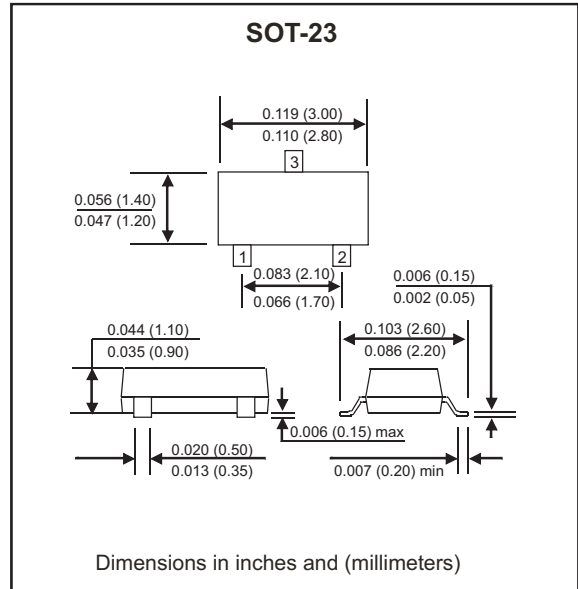


Features

- Fast switching diode.
- Surface mount package ideally suited for automatic insertion.
- For general purpose switching applications.
- High conductance.

Mechanical data

- Case: SOT-23
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.
- Weight: 0.008 gram.
- Marking: KA3



Maximum Rating (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Limits	Unit
Non-Repetitive peak reverse voltage	V_{RM}	100	V
Peak repetitive peak reverse voltage	V_{RRM}	75	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
RMS reverse voltage	$V_{R(RMS)}$	53	V
Forward continuous current	I_{FM}	500	mA
Average rectified output current	I_o	250	mA
Peak forward surge current	I_{FSM}	4.0	A
		2.0	
Power dissipation	P_d	350	mW
Thermal resistance-Junction to ambient air	$R_{\theta JA}$	357	°C/W
Storage temperature range	T_{STG}	-65 ~ +150	°C

Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Forward voltage	V_{F1}	$I_{F1}=5mA$	0.62	0.72	V
	V_{F2}	$I_{F2}=10mA$		0.855	
	V_{F3}	$I_{F3}=100mA$		1.0	
	V_{F4}	$I_{F4}=150mA$		1.25	
Reverse current	I_{R1}	$V_{R1}=75V$		2.5	μA
	I_{R2}	$V_{R2}=20V$		25	nA
Capacitance between terminals	C_T	$V_R=0V, f=1MHz$		4	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA, I_{rr}=0.1I_R, R_L=100\Omega$		4	nS

Characteristic Curves (CDST4448-G)

Fig.1 - Forward Characteristics

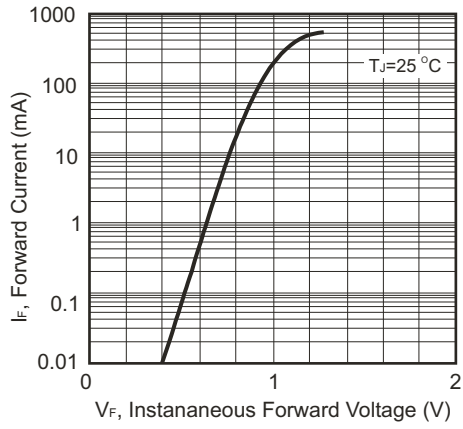


Fig.2 - Leakage Current vs Junction Temperature

